



Laser Diode ZBD-LD-525-16000M-FX

ZBD-LD-525-1600M-FX is a multimode laser diode with 1.6W CW output power at 525nm. Its beam pattern is linear with $10^\circ \times 1^\circ$ ($\theta_{//} \cdot \theta_{\perp}$). It is supplied in a 9mm floating mounted TO can with Zener Diode. The laser diode is suitable for opto-electronic applications.

■ Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Forward Current ($T_c=25^\circ\text{C}$)	I_f	2.3	A
Reverse Current ($T_c=25^\circ\text{C}$)	I_r (LD)	85	mA
Storage Temperature	T_{stg}	-40~85	$^\circ\text{C}$
Operating Case Temperature	T_c	0~65	$^\circ\text{C}$

■ Initial Electrical/Optical Characteristics ($T_c=25^\circ\text{C}$)

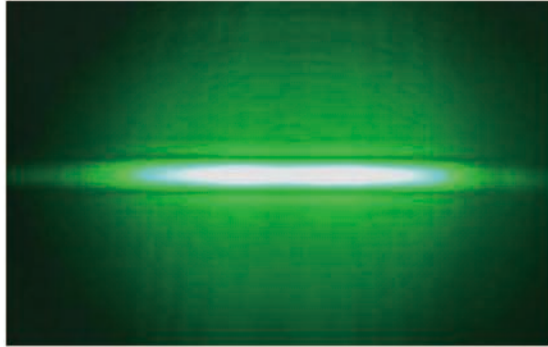
Parameter	Symbol	Condition	Min	Typ.	Max	Unit	
Optical Output Power	P_o	$I_f = 1.9\text{A}$	-	(1.6)	-	W	
Dominant Wavelength	λ_d	$I_f = 1.9\text{A}$	518	(525)	532	nm	
Threshold Current	I_{th}	CW	150	-	500	mA	
Slope Efficiency	η	CW	-	(1.1)	-	W/A	
Operating Voltage	V_{op}	$I_f = 1.9\text{A}$	4.0	-	6.0	V	
Beam Divergence*	Parallel	$\theta_{//}$	$I_f = 1.9\text{A}$	5	(11)	25	$^\circ$
	Perpendicular	θ_{\perp}	$I_f = 1.9\text{A}$	0.8	(1)	1.2	$^\circ$

() are reference figures.

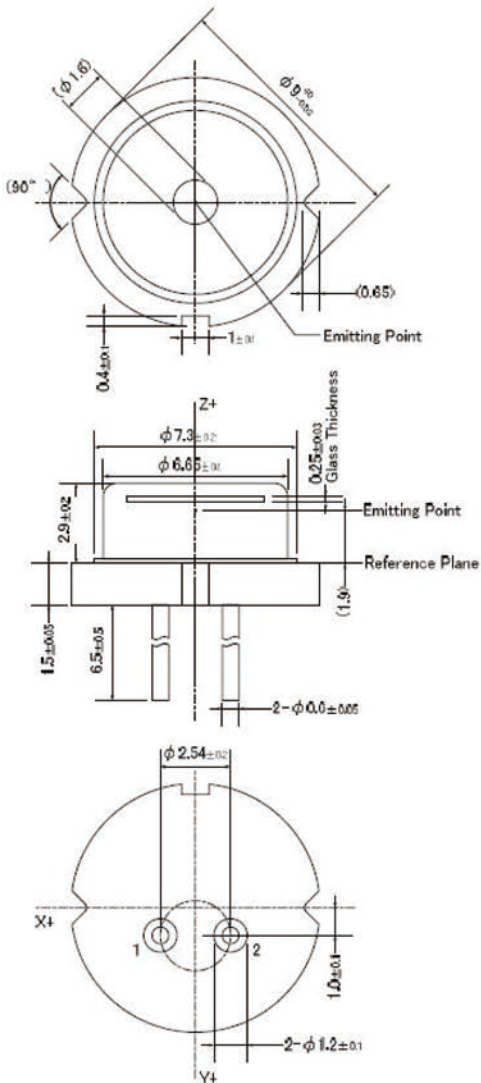
* Full angle at $1/e^2$ from peak intensity



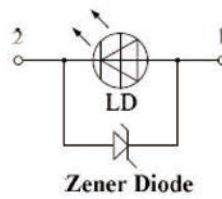
■ Beam Pattern



■ Outline Dimension (Unit: mm)



Connection



1. LD Anode
2. LD Cathode

Figures in () are reference purpose only.

Parts	Materials
Stem	Cu + Fe + Ni plating + Au plating
Lead	Ni-Fe-Co alloys + Ni plating + Au plating
Cap	Ni-Fe alloys + Ni plating
Glass	Borosilicate glass
Chip	Gallium nitride
Sub mount	Silicon carbide
Zener Diode	Silicon



■ Cautions

1. Laser light can damage the human eye and skin. Do not expose the eye and skin to any laser light directly or through optical lenses. Focused laser beam through optical instruments will increase the chance of eye hazard.
2. The laser needs a stable driver to avoid surges. The instantaneous reverse current and reverse voltage should not exceed the absolute maximum ratings, otherwise it will damage the laser diode.
3. Semiconductor lasers are sensitive to temperature, working at high temperatures will reduce the photoelectric conversion efficiency and accelerate the aging of laser diode. It should be used under adequate heat dissipation or cooling conditions.
4. The laser should be used at the rated current and rated power, the output power is too high will accelerate the aging of laser diode.
5. Semiconductor lasers are electrostatic sensitive devices, anti-static measures should be taken during storage and transportation.
6. Lasers should be stored or work in a dry, ventilated environment to prevent damage to the laser from condensation.
7. The light emitting surface (cavity surface) is the key parts of the laser diode, any handling to damage the cavity surface should be strictly prohibited. It should be ensured that the laser diode is not contaminated, and damaged in mechanical.

